

Product Overview

NLAS4717EP: Analog Switch, Dual SPDT, High Bandwidth, USB 1.1

For complete documentation, see the data sheet.

The NLAS4717EP is an advanced CMOS analog switch fabricated in sub-micron silicon gate CMOS technology. The device is a dual independent Single Pole Double Throw (SPDT) switch featuring low RDS(on) of 4.5 ohms at 3.0 V. The device also features guaranteed Break-Before-Make (BBM) switching, assuring the switches never short the driver. The NLAS4717EP is available in two small size packages: WQFN: 1.4 x 1.8 mm mm Microbump: 2.0 x 1.5 mm

Features

- Low RDS(on): 4.5 Ω @ 3.0V
- Matching Between the Switches $\pm 0.5 \Omega$
- Wide Voltage Range: 1.8 V to 5.5 V
- High Bandwidth > 90 MHz
- 1.65 V to 5.5 V Operating Range
- Low Threshold Voltages on Pins 4 and 8 (CTRL Pins)
- Ultra-Low Charge Injection ≤ 6.0 pC
- Low Standby Current: ICC=1.0nA (Max) @ TA=25°C
- *OVT on Pins 4 and 8 (CNTL Logic Pins)
- These are Pb-Free Devices

For more features, see the data sheet

Applications

- Cell Phones
- PDAs
- MP3s
- Digital Still Cameras
- USB 2.0 Full Speed (USB1.1) - 12 Mbps Compliant

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channels	Number of Switches	Configuration	I _{cc} Max (μ A)	r _{on} Max (Ω)	V _{CC} Min (V)	V _{CC} Max (V)	Package Type
NLAS4717EPFCT1G	0.6	Pb-free	Active	2	4	SPDT	1	4.5	1.8	5.5	Flip-Chip-10
		Halide free									
NLAS4717EPMTR2G	0.3733	Pb-free Halide free	Active	2	4	SPDT	1	4.5	1.8	5.5	WQFN-10

For more information please contact your local sales support at www.onsemi.com.

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